EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	118	(jun near2 suda or matsunami near2 hiroyuki or onojima near2 norio).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 09:29
L2	2	(jun near2 suda or matsunami near2 hiroyuki or onojima near2 norio).in. and (step$1terrace or terrace)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 09:30
S1	1	"10549683"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:38
S2	3	step$1terrace near4 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:15
S3	25	step near2 flow near4 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:17
S4	5	terrace near14 (sic or silicon near2 carbide) and (si or ga!) near5 irradiat$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:19
S5	119	(sic or silicon near2 carbide) and (si or ga!) near5 irradiat$6 near5 beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:20
S6	63	(sic or silicon near2 carbide) and (si or ga!) near5 irradiat$6 near5 beam and ("iii-v" or gan or aln)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:21
S7	20	(sic or silicon near2 carbide) near5 substrate and (si or ga!) near5 irradiat$6 near5 beam and ("iii-v" or gan or aln)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:21

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S8	81	(gan or aln) near15 (mbe or beam) near5 buffer and (sic or silicon near2 carbide) near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:28
S9	22	(gan or aln) near15 (mbe or beam) near5 buffer and (sic or silicon near2 carbide) near5 substrate and @py<"2003"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:30
S10	12	(gan or gallium near2 nitride) near15 (mbe) near5 buffer and (sic or silicon near2 carbide) near5 substrate and @py<"2003"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/09 16:30
S11	7	step near2 (sic or silicon near2 carbide) near4 terrace	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 11:16
S12	3	step near2 (sic or silicon near2 carbide) near4 offcut	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 11:17
S13	11	step near2 (sic or silicon near2 carbide) near4 flow	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 11:17
S14	2	"20060180077".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:44
S15	310	(sic or silicon near2 carbide) near15 irrad$7 near3 (ga! or si or silicon or gallium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:44
S16	233	(sic or silicon near2 carbide) near15 irrad$7 near3 (ga! or si or silicon or gallium) and @py<"2005"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:45
S17	31	(sic or silicon near2 carbide) near15 irrad$7 near3 (ga! or si or gallium) and @py<"2005"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:48

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S18	149	(sic or silicon near2 carbide) near2 buffer near16 (Gan or gallium near2 nitride or "iii-v")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:49
S19	115	(sic or silicon near2 carbide) near2 buffer near16 (Gan or gallium near2 nitride or "iii-v") and (sic or silicon near2 carbide) near2 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:54
S20	7	irradiat$6 near6 buffer near6 (Gan or gallium near2 nitride or "iii-v") and (sic or silicon near2 carbide) near2 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:54
S21	26	(mbe or beam) near6 buffer near6 (Gan or gallium near2 nitride or "iii-v") and (sic or silicon near2 carbide) near2 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 14:55
S22	23	(mbe or beam) near6 buffer near6 (Gan or gallium near2 nitride) and (sic or silicon near2 carbide) near2 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:06
S23	2	"20050098090".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:06
S24	1	"20050098090".pn. and aspir$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:40
S25	45	irradiat$6 near3 (ga! or gallium) and (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:40
S26	10	(US-20020059898-$ or US-20060194379-$ or US-20010015170-$ or US-20060180077-$ or US-20010008285-$).did. or (US-6165874-$ or US-6273950-$ or US-5760426-$ or US-6046464-$).did. or (JP-08203823-$).did.	US-PGPUB; USPAT; JPO	OR	ON	2008/01/16 15:55

S27	0	S26 and (oxide) near5 (hf or fluorine or fluoride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:56
S28	751	(sic or silicon near2 carbide) near10 (oxide or sio or "sio.sub.2" or "sio2") near5 (hf or fluorine or fluoride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:56
S29	5	(sic or silicon near2 carbide) near10 (oxide or sio or "sio.sub.2" or "sio2") near5 (hf or fluorine or fluoride) near5 (clean$5 or remove)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:58
S30	12	(sic or silicon near2 carbide) near10 (oxide or sio or "sio.sub.2" or "sio2") near5 (hf) near5 (clean$5 or remov$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:57
S31	4	(sic or silicon near2 carbide) near5 substrate near10 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near14 (clean$5 or remov$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:59
S32	2	(sic or silicon near2 carbide) near5 substrate near10 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near14 (gan or aln or nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 15:59
S33	14	(sic or silicon near2 carbide) near5 substrate near10 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:01
S34	1028	(sic or silicon near2 carbide) near10 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:01
S35	521	(sic or silicon near2 carbide) near10 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near16 (gan or aln or nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:01
S36	46	(sic or silicon near2 carbide) near10 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near16 (gan or aln)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:02

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S37	11549	(oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near16 (clean$5 or remov$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:02
S38	10606	(oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near6 (clean$5 or remov$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:03
S39	117	(oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near6 (clean$5 or remov$5) same (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:03
S40	81	(oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near6 (clean$5 or remov$5) same (sic or silicon near2 carbide) and @py<"2005"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:12
S41	2	(oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) near6 (clean$5 or remov$5) same (sic or silicon near2 carbide) same (gan or aln)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:04
S42	3	native near5 (oxide or sio or "sio.sub.2" or "sio2") near10 (hf or fluorine or fluoride) same (sic or silicon near2 carbide) near5 (substrate or wafer) and @py<"2005"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/16 16:14
S43	7021	hydrofluoric near10 (oxide) near10 (clean$6 or remov$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:17
S44	37	hydrofluoric near10 (oxide) near10 (clean$6 or remov$5) near16 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:25
S45	66	(gan or gallium near2 nitride) near5 buffer near15 (heat near2 treat$5 or anneal$5 or recrystal$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:44

S46	107	(gan or gallium near2 nitride) near5 buffer near15 (mbe or beam near2 epitax$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:45
S47	46	S46 and (anneal$5 or heat near2 treat$5 or recrystal$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:48
S48	2	S46 and (anneal$5 or heat near2 treat$5 or recrystal$7) near16 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:45
S49	16	S46 and (anneal$5 or heat near2 treat$5 or recrystal$7) and @py<"2004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:48
S50	6	S46 and (anneal$5 or heat near2 treat$5 or recrystal$7) and @py<"2004" and (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:59
S51	8	"1290721"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:53
S52	4	"10290721"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 15:53
S53	30	(sic or silicon near2 carbide) near10 step near2 terrace	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 16:45
S54	2	"6478871".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 16:46
S55	2	"20020179005".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 16:55

S56	2	"20060096524".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/18 16:55
S57	11	(gan or gallium near2 nitride) near10 (mbe) near15 (ultra$1high)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 01:59
S58	13	(gan or gallium near2 nitride) near10 (mbe) near15 (ultra$1high or uhv)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 02:01
S59	7	(gan or gallium near2 nitride) near10 (mbe or molecular near2 beam near2 epitax$6) near15 Pa	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 02:02
S60	2	(gan or gallium near2 nitride) and (mbe or molecular near2 beam near2 epitax$6) near15 Pa near5 less	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 02:03
S61	20	(gan or gallium near2 nitride) and (mbe or molecular near2 beam near2 epitax$6) near15 pressure near5 less	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 02:57